L Number	Hits	Search Text	I DP	1 m2
1	381		DB USPAT;	Time stamp
		transistor)) and (sige (silicon near5	US-PGPUB;	2002/09/30 10:59
		germanium))	EPO; JPO;	1
		, s, ,	DERWENT;	
i			IBM TDB	
6	64	((hbt (heterostructure adj bipolar adj	USPAT:	2002/09/30 11:29
		transistor)) and (sige (silicon near5	US-PGPUB;	2002/09/30 11:29
	,	germanium))) and mesa	EPO; JPO;	
			DERWENT:	
			IBM TDB	
7	61		USPAT;	2002/09/30 11:29
		transistor)) and (sige (silicon near5	US-PGPUB;	2002/03/30 11.29
1		germanium))) and mesa) and dop\$3	EPO; JPO;	
]		•	DERWENT;	
			IBM TDB	
8	46	i titting the corporate ad bibolar ad	USPĀT;	2002/09/30 11:30
		transistor)) and (sige (silicon near5	US-PGPUB;	
		germanium))) and mesa) and dop\$3) and	EPO; JPO;	]
		concentration	DERWENT;	
			IBM TDB	1
9	23		USPĀT;	2002/09/30 12:02
		transistor)) and (sige (silicon near5	US-PGPUB;	l i
		germanium))) and mesa) and dop\$3) and	EPO; JPO;	
		concentration) and depletion	DERWENT;	
10	7		IBM_TDB	
10	′	(((((hbt (heterostructure adj bipolar adj	USPĀT;	2002/09/30 11:31
		transistor)) and (sige (silicon near5	US-PGPUB;	[
		germanium))) and mesa) and dop\$3) and	EPO; JPO;	
		concentration) and depletion) and strained	DERWENT;	
12	2	////hht /hotomostmustume and him.	IBM_TDB	
12	۱ -	<pre>(((((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5</pre>	USPAT;	2002/09/30 11:33
		germanium))) and mesa) and dop\$3) and	US-PGPUB;	
		concentration) and (graded delta) near5	EPO; JPO;	
		dop\$3	DERWENT;	
11	2	(((((hbt (heterostructure adj bipolar adj	IBM_TDB USPAT:	2002/09/30 11:40
	_	transistor)) and (sige (silicon near5	US-PGPUB;	2002/09/30 11:40
	1	germanium))) and mesa) and dop\$3) and	EPO; JPO;	ļ
į	I	concentration) and delta near5 dop\$3	DERWENT;	ľ
ĺ	-	10010 doppy	IBM TDB	
13	23	(((((hbt (heterostructure adj bipolar adj	USPAT:	2002/09/30 12:02
	İ	transistor)) and (sige (silicon near5	US-PGPUB;	2002/03/30 12.02
1	ļ	germanium))) and mesa) and dop\$3) and	EPO; JPO;	
		concentration) and depletion) and deplet\$3	DERWENT;	
			IBM TDB	

L Number	Hits	Search Text	DB	Time stamp
2	40	((hbt (heterostructure adj bipolar adj	USPAT;	2002/09/30 10:48
ĺ		transistor)) and (sige (silicon near5	US-PGPUB;	1002,00,00 10.10
		germanium))) and depletion near5 region	EPO; JPO;	
			DERWENT;	
l <u>.</u> i			IBM TDB	
3	2	(((hbt (heterostructure adj bipolar adj	USPAT;	2002/09/30 10:50
		transistor)) and (sige (silicon near5	US-PGPUB;	
		germanium))) and depletion near5 region)	EPO; JPO;	i
		and strained near5 base	DERWENT;	
	_		IBM_TDB	
4	1	((hbt (heterostructure adj bipolar adj	USPAT;	2002/09/30 10:51
		transistor)) and (sige (silicon near5	US-PGPUB;	1
		germanium))) and strained near5 base	EPO; JPO;	
			DERWENT;	
1	201		IBM_TDB	i i
1	381	(hbt (heterostructure adj bipolar adj	USPAT;	2002/09/30 10:59
		transistor)) and (sige (silicon near5	US-PGPUB;	
1		germanium))	EPO; JPO;	
ŀ			DERWENT;	
6	64	//hhh /hahamash.mash.mash.	IBM_TDB	
٥	04	((hbt (heterostructure adj bipolar adj	USPAT;	2002/09/30 11:00
		transistor)) and (sige (silicon near5	US-PGPUB;	
		germanium))) and mesa	EPO; JPO;	[ ]
ĺ			DERWENT;	
			IBM_TDB	